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# BC556/557/558/559/560

# **Switching and Amplifier**

- High Voltage: BC556, V<sub>CEO</sub>= -65V
- Low Noise: BC559, BC560
- Complement to BC546 ... BC 550



1. Collector 2. Base 3. Emitter

# **PNP Epitaxial Silicon Transistor**

## Absolute Maximum Ratings Ta=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	TW. Ioo	$O_{Mrr}$
	: BC556	-80	V
	: BC557/560	-50	COV
	: BC558/559	-30	V
V <sub>CEO</sub>	Collector-Emitter Voltage	N WWW	1.00
	: BC556	-65	V
	: BC557/560	-45	V
	: BC558/559	-30	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	) V
Ic	Collector Current (DC)	-100	mA
P <sub>C</sub>	Collector Power Dissipation	500	mW
Tj	Junction Temperature	150	-∆()\\°C
T <sub>STG</sub>	Storage Temperature	-65 ~ 150	°C

## Electrical Characteristics Ta=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> = -30V, I <sub>E</sub> =0		4	-15	nA
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> = -5V, I <sub>C</sub> =2mA	110		800	700
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA I <sub>C</sub> = -100mA, I <sub>B</sub> = -5mA	TW	-90 -250	-300 -650	mV mV
V <sub>BE</sub> (sat)	Collector-Base Saturation Voltage	I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA I <sub>C</sub> = -100mA, I <sub>B</sub> = -5mA	W.L.	-700 -900		mV mV
V <sub>BE</sub> (on)	Base-Emitter On Voltage	$V_{CE}$ = -5V, $I_{C}$ = -2mA $V_{CE}$ = -5V, $I_{C}$ = -10mA	-600	-660	-750 -800	mV mV
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = -5V, I <sub>C</sub> = -10mA, f=10MHz	Olar	150		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = -10V, I <sub>E</sub> =0, f=1MHz	OM	F.	6	pF
NF	Noise Figure : BC556/557/558 : BC559/560 : BC559	$V_{CE}$ = -5V, $I_{C}$ = -200μA f=1KHz, $R_{G}$ =2KΩ $V_{CE}$ = -5V, $I_{C}$ = -200μA	I.CON	2 1 1.2	10 4 4	dB dB dB
	: BC560	$R_G=2K\Omega$ , $f=30\sim15000MHz$		1.2	2	dB

# h<sub>FF</sub> Classification

Classification	N. A.	В	C
h <sub>FE</sub>	110 ~ 220	200 ~ 450	420 ~ 800

# **Typical Characteristics**

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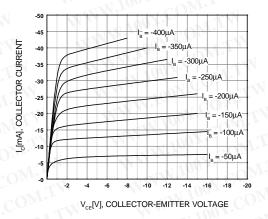


Figure 1. Static Characteristic

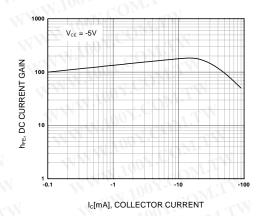


Figure 2. DC current Gain

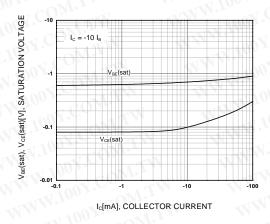


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

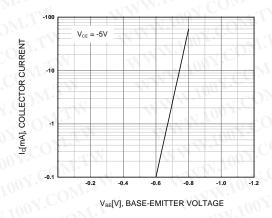


Figure 4. Base-Emitter On Voltage

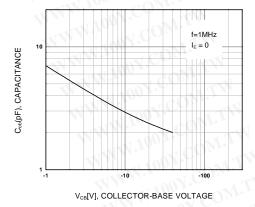


Figure 5. Collector Output Capacitance

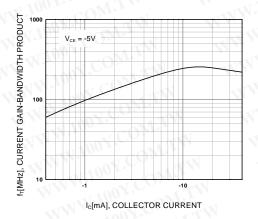


Figure 6. Current Gain Bandwidth Product

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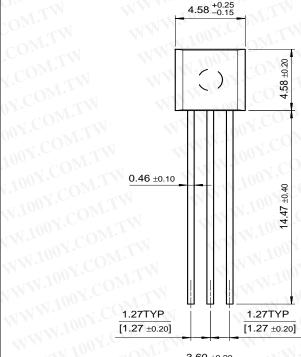
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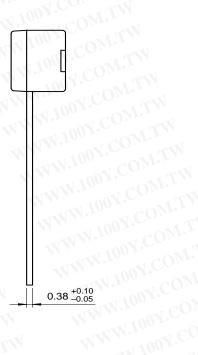
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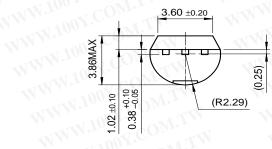
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